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TMT	A1	4,058,430	11/15/77	Suntola et al.	156	611	11/25/19	975
1	A2	4,389,973	06/28/83	Suntola et al.	118	725	12/11/1	981
	А3	4,413,022	11/01/83	Suntola et al.	427	255.2	06/21/1	979
	A4	4,486,487	12/04/84	Skarp	428	216	04/25/1	983
	A5	4,767,494	08/30/88	Kobayashi et al	. 156	606	09/19/1	986
	A6	4,806,321	02/21/89	Nishizawa et al	. 422	245	07/21/1	985
	A7	4,829,022	05/09/89	Kobayashi et al	l. 437	107	12/09/19	986
	A8	4,834,831	05/30/89	Nishizawa et al	. 156	611	09/04/1	987
	A9	4,838,983	06/13/89	Schumaker et al.	156	613	03/18/1	988
	A10	4,838,993	06/13/89	Aoki et al.	156	643	12/03/1	987
	A11	4,840,921	06/20/89	Matsumoto	437	89	06/30/1	988
	A12	4,845,049	07/04/89	Sunakawa	437	81	03/28/1	988
TMT	A13	4,859,625	08/22/89	Nishizawa et al	. 437	81	11/20/1	987
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TMT	B1	01/66832 A2	09/13/2001	wo	C30B	16/44		X
1	B2	01/40541 A1	06/07/2001	wo	C23C	16/40		X
	В3	01/36702 A1	05/25/2001	wo	C23C	16/00		×
T	B4	01/29893 A1	04/26/2001	wo	H01L	21/768		Х
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TMT	C1	Hultman, et al., "Revi Metalikunde, 90(10)	Oct. 1999), pp. 803	3-813.				
TMT	C2	Klaus, et al., "Atomic Surface Review & Le	Layer Deposition o tters, 6(3&4) (1999)	f SiO₂ Using Catalyze), pp. 435-448.				1
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TMT	A28	5,225,366	07/06/93	Yoder	437	108	06/22/19	990
1	A29	5,246,536	09/21/93	Nishizawa et al	. 156	610	03/10/19	989
	A30	5,250,148	10/05/93	Nishizawa et al	. 156	611	11/12/19	991
	A31	5,254,207	10/19/93	Nishizawa et al	. 156	601	11/30/19	992
	A32	5,256,244	10/26/93	Ackerman	156	613	02/10/1	992
	A33	5,270,247	12/14/93	Sakuma et al.	437	133	07/08/1	992
	A34	5,278,435	01/11/94	Van Hove et al.	257	184	06/08/1	992
1	A35	5,281,274	01/25/94	Yoder	118	697	02/04/1	993
	A36	5,290,748	03/01/94	Knuuttila et al.	502	228	07/16/1	992
	A37	5,294,286	03/15/94	Nishizawa et al	. 156	610	01/12/1	993
	A38	5,296,403	03/22/94	Nishizawa et al	. 437	133	10/23/1	992
	A39	5,300,186	04/05/94	Kitahara et al.	156	613	04/07/1	992
TMT	A40	5,311,055	05/10/94	Goodman et al.	257	593	11/22/1	991
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TNY	T A41	5,316,615	05/31/94	Copel	117	95	03/09/1	993
1	A42	5,316,793	05/31/94	Wallace et al.	427	248.1	07/27/1	992
	A43	5,330,610	07/19/94	Eres et al.	117	86	05/28/1	993
$\neg \vdash$	A44	5,336,324	08/09/94	Stall et al.	118	719	12/04/1	991
	A45	5,338,389	08/16/94	Nishizawa et al	. 117	89	04/21/1	993
	A46	5,348,911	09/20/94	Jurgensen et a	1. 117	91	04/26/1	993
	A47	5,374,570	12/20/94	Nasu et al.	437	40	08/19/1	993
	A48	5,395,791	03/07/95	Cheng et al.	437	105	10/20/1	993
\top	A49	5,438,952	08/08/1995		117	84	01/31/1	994
	A50	5,439,876	08/08/95	Graf et al.	505	447	08/16/1	993
	A51	5,441,703	08/15/95	Jurgensen	422	129	03/29/1	994
	A52	5,443,033	08/22/95	Nishizawa et al	. 117	86	03/11/1	994
	A53	5,443,647	08/22/95	Aucoin et al.	118	723 ME	07/11/1	994
JMT	A54	5,455,072	10/03/95	Bension et al.	427	255.7	11/18/1	992
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1	B14	00/16377 A2	03/23/2000	wo	H01L			Х
	B15	00/15881 A2	03/23/2000	WO	C30B			Х
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TMT	A55	5,458,084	10/17/95	Thorne et al.	117	89	12/09/1	993	
1	A56	5,469,806	11/28/95	Mochizuki et al	. 117	97	08/20/1	993	
	A57	5,480,818	01/02/96	Matsumoto et al.	437	40	02/09/1	993	
	A58	5,483,919	01/16/96	Yokoyama et al.	117	89	08/17/1	994	
	A59	5,484,664	01/16/96	Kitahara et al.	428	641	01/21/1	994	
	A60	5,503,875	04/02/96	Imai et al.	427	255.3	03/17/1	994	
	A61	5,521,126	05/28/96	Okamura et al.	437	235	06/22/1	994	
	A62	5,527,733	06/18/96	Nishizawa et al	. 437	160	02/18/1	02/18/1994	
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.	A64	5,540,783	07/30/96	Eres et al.	118	725	05/26/1	994	
	A65	5,601,651	02/11/97	Watabe	118	715	12/14/1	994	
	A66	5,616,181	04/01/97	Yamamoto et al.	118	723 ER	11/21/1	995	
TMT	A67	5,637,530	06/10/97	Gaines et al.	114	105	06/10/1	996	
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	B18	99/29924 A1	06/17/1999	wo	C23C `	16/04		X	
	B19	99/01595	01/14/1999	wo	C30B	25/14		X	
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TMT	A68	5,641,984	06/24/97	Aftergut et al.	. 2	257	433	0	8/19/19	94
1	A69	5,644,128	07/01/97	Wollnik et al.	2	250	251	C	8/25/19	94
	A70	5,693,139	12/02/97	Nishizawa et	al. 1	17	89	C	6/15/19	93
	A71	5,705,224	01/06/98	Murota et al.	4	127	248.1		1/31/19	95
	A72	5,707,880	01/13/98	Aftergut et al.	4	137	3		1/17/19	97
	A73	5,711,811	01/27/98	Suntola et al.	1	18	711	1	1/28/19	95
	A74	5,730,802	03/24/98	Ishizumi et al	. 1	18	719	1	12/27/1996	
	A75	5,747,113	05/05/98 05/12/98	Tsai	427	127	255.5		07/29/1996	
	A76	5,749,974		3 Habuka et al.	. 1	118	725	0	07/13/1995	
	A77	5,796,116	08/18/98	Nakata et al.	2	257	66	0	7/25/19	95
	A78	5,807,792	09/15/98	llg et al.	4	138	758	1	2/18/19	96
T	A79	5,830,270	11/03/98	McKee et al.	1	17	106	C	8/05/19	96
TMT	A80	5,835,677	11/10/98	Li et al.	3	392	401	1	0/03/19	96
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TMT	A81	5,851,849	12/22/98	Comizzoli et al.	438	38	05/22/1	997
1	A82	5,855,675	01/05/99	Doering et al.	118	719	03/03/1	997
	A83	5,855,680	01/05/99	Soininen et al.	118	719	11/28/1	995
	A84	5,858,102	01/12/99	Tsai	118	719	02/14/1	998
	A85	5,904,565	05/18/1999	Nguyen, et al.	438	687	07/17/1	997
	A86	5,923,056	07/13/99	Lee et al.	257	192	03/12/1	998
	A87	5,923,985	07/13/99	Aoki et al.	438	301	01/14/1	997
	A88	5,925,574	07/20/99	Aoki et al.	437	31	04/10/1	992
	A89	5,942,040	08/24/99	Kim et al.	118	726	08/27/1	997
	A90	5,947,710	09/07/1999	Cooper, et al.	418	63	06/16/1	997
1	A91	6,001,669	12/14/99	Gaines et al.	438	102	07/21/1	992
	A92	6,015,590	01/18/00	Suntola et al.	427	255.23	11/28/1	995
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TMT	A94	6,036,773	03/14/00	Wang et al.	117	97	03/27/1	997	
1	A95	6,042,652	03/28/00	Hyun et al.	118	719	09/07/1	999	
	A96	6,043,177	03/28/00	Falconer et al	502	4	01/21/1	997	
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1	A102	6,174,809	01/16/2001	Kang, et al.	438	682	12/15/1	998	
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TMI	- C14	Elers, et al., "N 468-474.	bC15 as a prec	ursor in atomic lay	er epitaxy", A	Appl. Surf. So	i., Vol. 82/8	3 (1994), p	
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